L Number	Hits	Search Text	DB	Time stamp
1	5810	gamma$1butyrolactone	USPAT; US-PGPUB	2002/07/08 18:59
4	191	adamantyl adj methacrylate	USPAT; US-PGPUB	2002/07/08 18:57
7	30	gamma$1butyrolactone and (adamantyl adj methacrylate)	USPAT; US-PGPUB	2002/07/08 18:57
10	3698	gamma$1butyrolactone same solvent	USPAT; US-PGPUB	2002/07/08 19:00
13	2112	gamma$1butyrolactone not (gamma$1butyrolactone same solvent)	USPAT; US-PGPUB	2002/07/08 19:00
16	2	(gamma$1butyrolactone not (gamma$1butyrolactone same solvent)) and (adamantyl adj methacrylate)	USPAT; US-PGPUB	2002/07/08 19:00

PGMEA 91% 700 ml
5% 300 ml
1000 ml

Same @ as 09/770,212 FD 1/29/01

L10 ANSWER 1 OF 18 CAPLUS COPYRIGHT 2002 ACS
AN 2002:429451 CAPLUS
DN 137:26108
TI Positive-working photoresist composition
IN Hada, Hideo; Fujimura, Satoshi; Sasaki, Kazuhito; Iwai, Takeshi
PA Japan
SO U.S. Pat. Appl. Publ., 7 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2002068238	A1	20020606	US 2001-996676	20011130
	JP 2002169292	A2	20020614	JP 2000-369225	20001204
PRAI	JP 2000-369225	A	20001204		

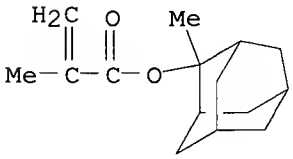
CF 1 and 4

AB The invention discloses a pos.-working photoresist compn. suitable for patterning light-exposure with light having a wavelength of .ltoreq. 200 nm. The photoresist compn. comprises (1) a resinous compd. capable of being imparted with increased soly. in an aq. alk. soln. by interaction with an acid, (2) a radiation-sensitive acid generating compd. capable of generating an acid by irradn. with a radiation and (3) an org. solvent. The resinous compd. is a copolymer consisting of a combination of three types of specific (meth)acrylate units as the monomeric units. The patterned resist layer formed from the photoresist compn. has an advantage in respect of decreased line slimming caused by electron beam irradn. in SEM inspection.

IT **348631-34-5**
RL: TEM (Technical or engineered material use); USES (Uses)
(resin; pos.-working photoresist compn. contg.)
RN 348631-34-5 CAPLUS
CN 2-Propenoic acid, 2-methyl-, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate and tetrahydro-5-oxo-3-furanyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

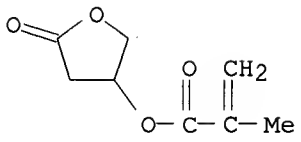
CM 1

CRN 177080-67-0
CMF C15 H22 O2



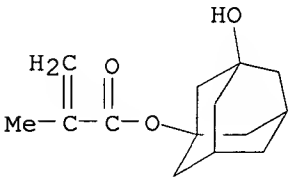
CM 2

CRN 130224-95-2
CMF C8 H10 O4



CM 3

CRN 115372-36-6
CMF C14 H20 O3



L10 ANSWER 2 OF 18 CAPLUS COPYRIGHT 2002 ACS
AN 2002:381311 CAPLUS
DN 136:409016
TI Acrylic polymer compound for photoresist and manufacture thereof
IN Tsutsumi, Kiyoharu; Funaki, Katsunori
PA Daicel Chemical Industries, Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 9 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE

Same @ AS 09/770,212 FD 1/29/01

N 2002:119352 CAPLUS
DN 136:175472
TI Positive photosensitive composition for photofabrication using deep UV ray
IN Kodama, Kunihiko; Aoai, Toshiaki
PA Fuji Photo Film Co., Ltd., Japan
SO Eur. Pat. Appl., 120 pp.
CODEN: EPXXDW
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	EP 1179750	A1	20020213	EP 2001-117796	20010802
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
	JP 2002122994	A2	20020426	JP 2001-188670	20010621
	US 2002051933	A1	20020502	US 2001-921691	20010806
PRAI	JP 2000-240059	A	20000808		

AB A pos. photosensitive compn. comprises: (A) a compd. generating an acid upon irradn. with one of an actinic ray and radiation; (B) a resin contg. a monocyclic or polycyclic alicyclic hydrocarbon structure and increasing the soly. to an alkali developer by the action of an acid; and (C) an onium salt of carboxylic acid. The present invention relates to a pos. photosensitive compn. for use in the prodn. process of a semiconductor such as IC, in the prodn. of a circuit board such as liq. crystal and thermal head, and in other photofabrication processes.

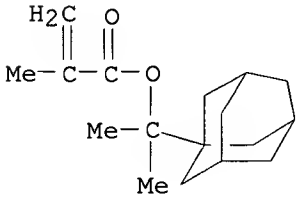
IT **398140-38-0P 398141-11-2P**
RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(resin; deep UV photofabrication pos. photoresist compn. contg.)

RN 398140-38-0 CAPLUS
CN 2-Propenoic acid, 2-methyl-, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 1-methyl-1-tricyclo[3.3.1.13,7]dec-1-ylethyl 2-methyl-2-propenoate and tetrahydro-5-oxo-3-furanyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 279218-76-7
CMF C17 H26 O2

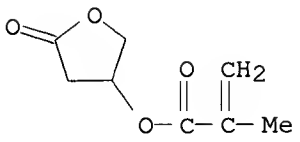
X1



921,691
Ready for actn

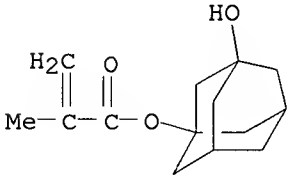
CM 2

CRN 130224-95-2
CMF C8 H10 O4



CM 3

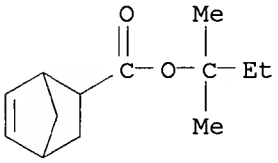
CRN 115372-36-6
CMF C14 H20 O3



RN 398141-11-2 CAPLUS
CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate and tetrahydro-5-oxo-3-furanyl 2-propenoate (9CI) (CA INDEX NAME)

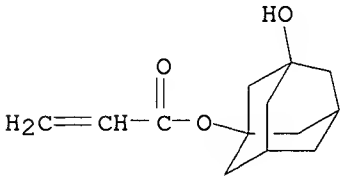
CM 1

CRN 398140-58-4
CMF C13 H20 O2



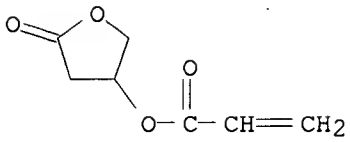
CM 2

CRN 216581-76-9
CMF C13 H18 O3



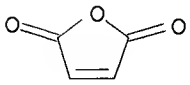
CM 3

CRN 130225-01-3
CMF C7 H8 O4



CM 4

CRN 108-31-6
CMF C4 H2 O3



RE.CNT 13 THERE ARE 13 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L10 ANSWER 5 OF 1